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Vishay Semiconductors

Thyristor High Voltage, Phase Control SCR, 10 A



3L TO-220AB

| PRIMARY CHARACTERISTICS | | | | | |
|------------------------------------|------------------|--|--|--|--|
| I _{T(AV)} 6.5 A | | | | | |
| V _{DRM} /V _{RRM} | 800 V | | | | |
| V _{TM} | 1.15 V | | | | |
| I _{GT} | 15 mA | | | | |
| TJ | -40 °C to 125 °C | | | | |
| Package | 3L TO-220AB | | | | |
| Circuit configuration | Single SCR | | | | |

FEATURES

- Designed and qualified according to JEDEC[®]-JESD 47

 RoHS
- 125 °C max. operating junction temperature
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

APPLICATIONS

• Typical usage is in input rectification crowbar (soft star) and AC switch in motor control, UPS, welding, and battery charge

DESCRIPTION

The VS-10TTS08... high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

| OUTPUT CURRENT IN TYPICAL APPLICATIONS | | | | | | |
|--|---------------------|--------------------|-------|--|--|--|
| APPLICATIONS | SINGLE-PHASE BRIDGE | THREE-PHASE BRIDGE | UNITS | | | |
| Capacitive input filter $T_A = 55 \text{ °C}, T_J = 125 \text{ °C},$ common heatsink of 1 °C/W | 13.5 | 17 | A | | | |

| MAJOR RATINGS AND CHARACTERISTICS | | | | | |
|------------------------------------|-------------------------------|-------------|-------|--|--|
| PARAMETER | TEST CONDITIONS | VALUES | UNITS | | |
| I _{T(AV)} | Sinusoidal waveform | 6.5 | ٨ | | |
| I _{T(RMS)} | | 10 | A | | |
| V _{RRM} /V _{DRM} | | 800 | V | | |
| I _{TSM} | | 110 | А | | |
| V _T | 6.5 A, T _J = 25 °C | 1.15 | V | | |
| dV/dt | | 150 | V/µs | | |
| dl/dt | | 100 | A/µs | | |
| TJ | Range | -40 to +125 | °C | | |

| VOLTAGE RATINGS | | | |
|-----------------|---|--|---|
| PART NUMBER | V _{RRM} , MAXIMUM PEAK REVERSE VOLTAGE V | V _{DRM} , MAXIMUM PEAK DIRECT VOLTAGE V | I _{RRM} /I _{DRM} AT 125 °C mA |
| VS-10TTS08-M3 | 800 | 800 | 1.0 |

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| ABSOLUTE MAXIMUM RATINGS | | | | | |
|---|----------------------------------|--|---|-------|------------------|
| PARAMETER | SYMBOL | TEST CONDITIONS | VALUES | UNITS | |
| Maximum average on-state current | I _{T(AV)} | T 110 °C 190° condu | ation half aine wave | 6.5 | |
| Maximum RMS on-state current | I _{T(RMS)} | T _C = 112 °C, 180° conduc | cuon nan sine wave | 10 | А |
| Maximum peak, one-cycle, | | 10 ms sine pulse, rated V | / _{RRM} applied, T _J = 125 °C | 95 | A |
| non-repetitive surge current | I _{TSM} | 10 ms sine pulse, no volta | age reapplied, T _J = 125 °C | 110 | |
| Maximum I ² t for fusing | l ² t | 10 ms sine pulse, rated V | / _{RRM} applied, T _J = 125 °C | 45 | A20 |
| Maximum 1-t for fusing | 1-1 | 10 ms sine pulse, no volta | age reapplied, T _J = 125 °C | 64 | A ² s |
| Maximum I ² √t for fusing | l²√t | t = 0.1 ms to 10 ms, no voltage reapplied, T_J = 125 °C | | 640 | A²√s |
| Maximum on-state voltage drop | V _{TM} | 6.5 A, T _J = 25 °C | | 1.15 | V |
| On-state slope resistance | r _t | T 105.00 | | 17.3 | mΩ |
| Threshold voltage | V _{T(TO)} | T _J = 125 °C | | 0.85 | V |
| Maximum reverse and direct leakage | 1 /1 | T _J = 25 °C | | 0.05 | - |
| current | I _{RM} /I _{DM} | T _J = 125 °C | $V_{R} = Rated V_{RRM}/V_{DRM}$ | 1.0 | |
| Typical holding current | Ι _Η | Anode supply = 6 V, resistive load, initial I_T = 1 A, T_J = 25 °C | | 30 | mA |
| Maximum latching current | ١L | Anode supply = 6 V, resistive load, $T_J = 25 \ ^\circ C$ | | 50 | |
| Maximum rate of rise of off-state voltage | dV/dt | $T_J = T_J max.$, linear to 80 %, $V_{DRM} = R_g - k = Open$ | | 150 | V/µs |
| Maximum rate of rise of turned-on current | dl/dt | | | 100 | A/µs |

| TRIGGERING | | | | | |
|--|--------------------|--|--------|-------|--|
| PARAMETER | SYMBOL | TEST CONDITIONS | VALUES | UNITS | |
| Maximum peak gate power | P _{GM} | | 8.0 | W | |
| Maximum average gate power | P _{G(AV)} | | 2.0 | vv | |
| Maximum peak positive gate current | +I _{GM} | | 1.5 | А | |
| Maximum peak negative gate voltage | -V _{GM} | | 10 | V | |
| | I _{GT} | Anode supply = 6 V, resistive load, T_J = - 65 °C | 20 | | |
| Maximum required DC gate current to trigger | | Anode supply = 6 V, resistive load, $T_J = 25 \text{ °C}$ | 15 | mA | |
| | | Anode supply = 6 V, resistive load, $T_J = 125 \text{ °C}$ | 10 | | |
| | | Anode supply = 6 V, resistive load, T_J = - 65 °C | 1.2 | | |
| Maximum required DC gate voltage to trigger | V _{GT} | Anode supply = 6 V, resistive load, $T_J = 25 \ ^{\circ}C$ | 1 | v | |
| | | Anode supply = 6 V, resistive load, $T_J = 125 \text{ °C}$ | 0.7 | v | |
| Maximum DC gate voltage not to trigger | V_{GD} | T 125 °C. V Deted volue | 0.2 | | |
| Maximum DC gate current not to trigger | I _{GD} | T _J = 125 °C, V _{DRM} = Rated value | 0.1 | mA | |

| SWITCHING | | | | | | |
|-------------------------------|-----------------|---------------------------|--------|-------|--|--|
| PARAMETER | SYMBOL | TEST CONDITIONS | VALUES | UNITS | | |
| Typical turn-on time | t _{gt} | T _J = 25 °C | 0.8 | | | |
| Typical reverse recovery time | t _{rr} | T 105 %C | 3 | μs | | |
| Typical turn-off time | tq | - T _J = 125 °C | 100 | | | |

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VS-10TTS08-M3

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| THERMAL AND MECHANICAL SPECIFICATIONS | | | | | |
|---|---------|-----------------------------------|--------------------------------------|-------------|------------|
| PARAMETER | | SYMBOL | TEST CONDITIONS | VALUES | UNITS |
| Maximum junction and storage temperature range | | T _J , T _{Stg} | | -40 to +125 | °C |
| Maximum thermal resistance, junction to case | | R _{thJC} | DC operation | 1.5 | |
| Maximum thermal resistance, junction to ambient | | R _{thJA} | | 62 | °C/W |
| Typical thermal resistance, case to heatsink | | R _{thCS} | Mounting surface, smooth and greased | 0.5 | |
| Approvimate weight | | | | 2 | g |
| Approximate weight | | | | 0.07 | oz. |
| Mounting torque | minimum | | | 6 (5) | kgf · cm |
| Mounting torque — | maximum | | | 12 (10) | (lbf ⋅ in) |
| Marking device | | | Case style 3L TO-220AB | 10TTS | S08 |

Maximum Average On-State Power Loss (W)

Maximum Average On-State Power Loss (W)

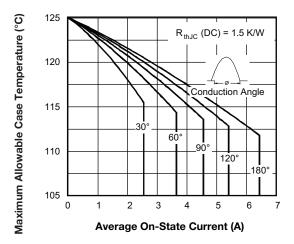
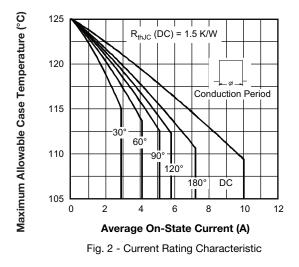
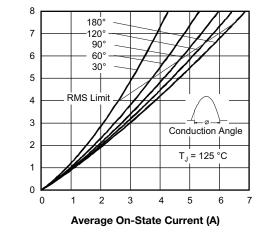


Fig. 1 - Current Rating Characteristics







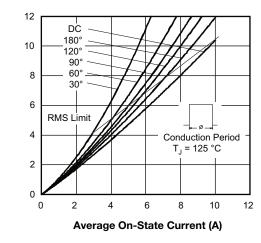


Fig. 4 - On-State Power Loss Characteristics

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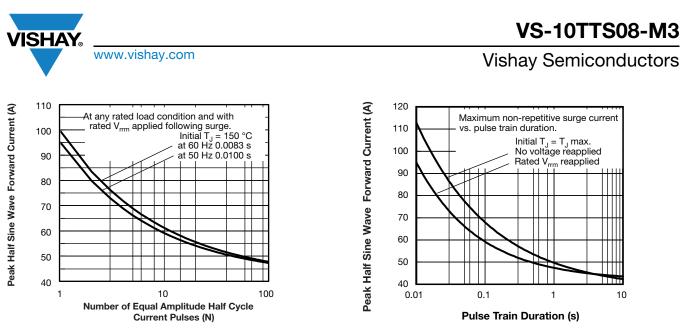


Fig. 5 - Maximum Non-Repetitive Surge Current



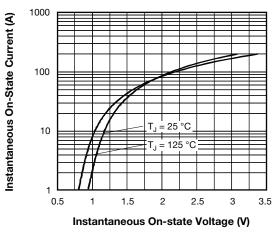
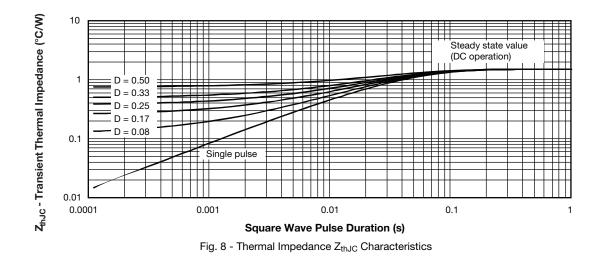


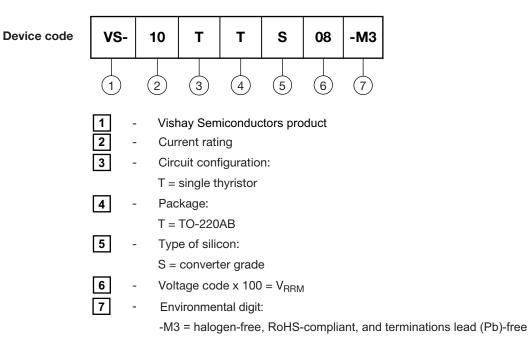
Fig. 7 - On-State Voltage Drop Characteristics





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ORDERING INFORMATION TABLE



| ORDERING INFORMATION (Example) | | | | | |
|--------------------------------|------------------|------------------------|--------------------------|--|--|
| PREFERRED P/N | QUANTITY PER T/R | MINIMUM ORDER QUANTITY | PACKAGING DESCRIPTION | | |
| VS-10TTS08-M3 | 50 | 1000 | Antistatic plastic tubes | | |

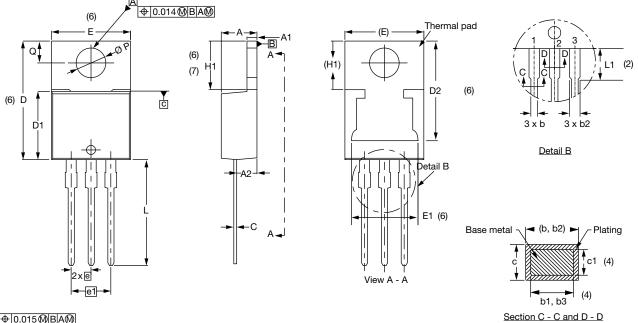
| LINKS TO RELATED DOCUMENTS | | | | |
|-------------------------------------|--------------------------|--|--|--|
| Dimensions www.vishay.com/doc?96154 | | | | |
| Part marking information | www.vishay.com/doc?95028 | | | |



Vishay Semiconductors

3L TO-220AB

DIMENSIONS in millimeters and inches



⊕0.015@BA@





| SYMBOL | MILLIN | IETERS | INC | HES | NOTES |
|---------|--------|--------|-------|-------|-------|
| STNIBOL | MIN. | MAX. | MIN. | MAX. | NOTES |
| А | 4.25 | 4.65 | 0.167 | 0.183 | |
| A1 | 1.14 | 1.40 | 0.045 | 0.055 | |
| A2 | 2.50 | 2.92 | 0.098 | 0.115 | |
| b | 0.69 | 1.01 | 0.027 | 0.040 | |
| b1 | 0.38 | 0.97 | 0.015 | 0.038 | 4 |
| b2 | 1.20 | 1.73 | 0.047 | 0.068 | |
| b3 | 1.14 | 1.73 | 0.045 | 0.068 | 4 |
| С | 0.36 | 0.61 | 0.014 | 0.024 | |
| c1 | 0.36 | 0.56 | 0.014 | 0.022 | 4 |
| D | 14.85 | 15.35 | 0.585 | 0.604 | 3 |
| D1 | 8.38 | 9.02 | 0.330 | 0.355 | |

| Conforms to JEDEC® | outline | TO-220AB |
|--------------------|---------|----------|
| | ouume | 10-220AD |

| SYMBOL | MILLIMETERS | | INCHES | | NOTES |
|--------|-------------|-------|--------|-------|-------|
| | MIN. | MAX. | MIN. | MAX. | NOTES |
| D2 | 11.68 | 12.88 | 0.460 | 0.507 | 6 |
| Е | 10.11 | 10.51 | 0.398 | 0.414 | 3, 6 |
| E1 | 6.86 | 8.89 | 0.270 | 0.350 | 6 |
| е | 2.41 | 2.67 | 0.095 | 0.105 | |
| e1 | 4.88 | 5.28 | 0.192 | 0.208 | |
| H1 | 6.09 | 6.48 | 0.240 | 0.255 | 6, 7 |
| L | 13.52 | 14.02 | 0.532 | 0.552 | |
| L1 | 3.32 | 3.82 | 0.131 | 0.150 | 2 |
| ØР | 3.54 | 3.91 | 0.139 | 0.154 | |
| Q | 2.60 | 3.00 | 0.102 | 0.118 | |
| | | | | | |

Notes

⁽²⁾ Lead dimension and finish uncontrolled in L1

⁽⁴⁾ Dimension b1, b3, and c1 apply to base metal only

- ⁽⁶⁾ Thermal pad contour optional within dimensions E, H1, D2, and E1
- ⁽⁷⁾ Outline conforms to JEDEC[®] TO-220, except D2 (minimum)

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 $^{^{(1)}\,}$ Dimensioning and tolerancing as per ASME Y14.5M-1994

⁽³⁾ Dimension D, D1, and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body

⁽⁵⁾ Controlling dimensions: inches



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